



CM2N60 N-channel VDMOS

*Applications :

- ◆ Power adapter, Linear amplification and Power switching circuit

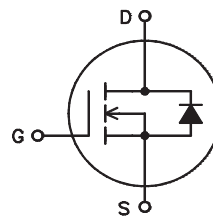
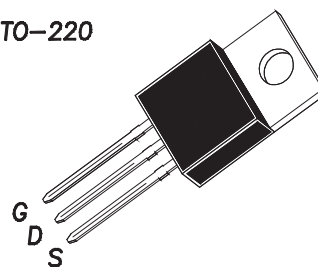
*Features:

- ◆ Low on-resistance, low input capacitance
- ◆ High-speed switching
- ◆ 100% avalanche tested

*Notice:

- ◆ Anti-static

TO-220



G.Gate D.Drain S.Source

Absolute Maximum Ratings: (Tc=25°C unless specified)

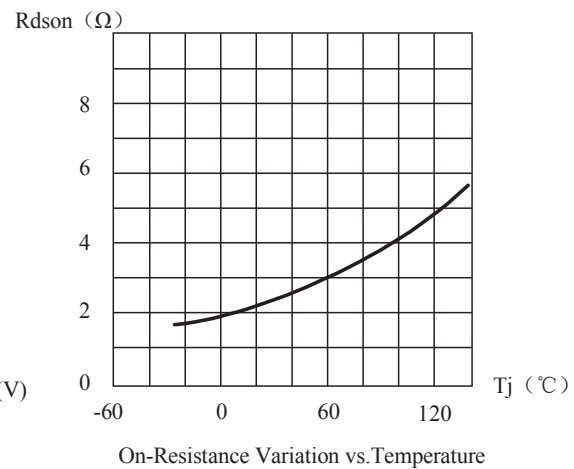
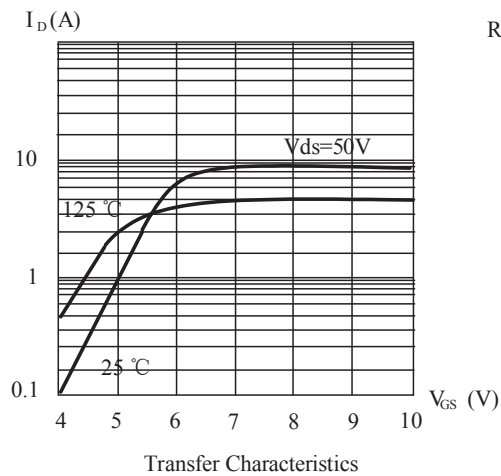
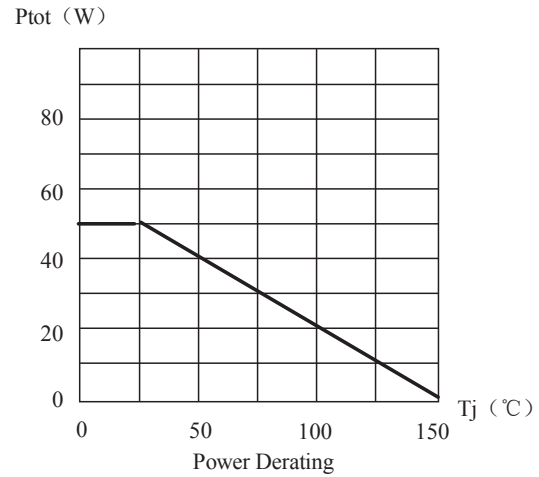
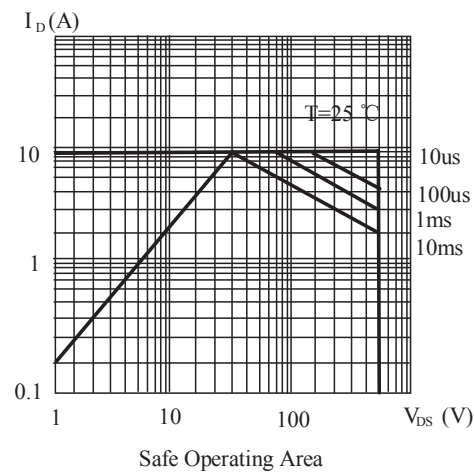
Parameter	Symbol	Value	Unit
Drain Current (continuous)	I_D	2	A
Gate-Source Voltage	V_{GS}	± 30	V
Avalanche current	I_{AR}	2.2	A
Rthj-case	$R_{\theta JC}$	2.5	°C /W
Power Dissipation	P_{tot}	50	W
Junction Temperature	T_{jm}	150	°C
Storage Temperature	T_{stg}	- 55 ~ 150	°C

Electronical Characteristic: (Tc=25°C unless specified)

Parameter	Symbol	Test conditions	Min.	TYP.	Max.	Unit
Drain-Source Voltage	V_{DS}	$V_{GS}=0V, I_D=250\mu A$	600			V
Static drain-source on resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=1.2A$			4.4	Ω
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2		4	V
Forward transconductance	g_{fs}	$V_{DS}=50V, I_D=1.0A$	1.4			S
Zero gate voltage drain current	I_{DSS}	$V_{DS}=600V, V_{GS}=0V$			25	μA
Gate-body leakage current	I_{GSS}	$V_{GS}=\pm 30V$			± 100	nA
Turn-off delay time	$t_d(off)$	$V_{DD}=300V, I_D=2.0A$ $R_G=18\Omega, R_D=150\Omega$		20		nS
Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=25V$ $f=1.0MHz$		350		pF
a: Pulse test : $t_p \leq 300\mu s, \delta \leq 2\%$						



Typical characteristics





Package Dimensions

TO-220 (Unit: mm, Tolerance ± 0.1 mm unless specified)

